

Online Examinations (Even Sem/Part-I/Part-II Examinations 2020 - 2021)

Course Name - -VLSI Devices and Design

Course Code - PCC-EC603

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Answer all the questions. Each question carry one mark.

9. 1. Moore was co-founder of

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- TCS
- Infosys
- Intel
- Wipro

10. 2. Medium scale integration has _____ logic gates.

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- 13 to 99
- 1 to 12
- 100 to 9,999
- 10,000 to 99,999

11. 3. As die size shrinks, the complexity of making the photomasks _____

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- increases
- decreases
- remains the same
- cannot be determined

12. 4. What is the design flow of VLSI system? i. architecture design ii. circuit design iii. logic design iv. physical design

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- ii-i-iii-iv
- iv-i-iii-ii
- iii-ii-i-iv
- i-iii-ii-iv

13. 5. Which is the high level representation of VLSI design?

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- architect design
- logic design
- circuit design
- physical design

14. 6. Gate minimization technique is used to simplify the logic.

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- true
- false
- In the case of Silicon, even if the number of the gate is minimised, logic will not be simplified
- In the case of Ge, even if the number of the gate is minimised, logic will not be simplified

15. 7. nMOS fabrication process is carried out in _____

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- thin wafer of a single crystal
- thin wafer of multiple crystals
- thick wafer of a single crystal
- thick wafer of a multiple crystal

16. 8. What kind of layer is provided upon which other layers may be deposited and patterned.

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- insulating
- conducting
- silicon
- semiconducting

17. 9. In nMOS device, gate material could be _____

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- silicon
- polysilicon
- boron
- phosphorus

18. 10. Electronics are characterized by _____

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- low cost
- low weight and volume
- reliability
- low cost, low weight and volume, reliability

19. 11. nMOS devices are formed in _____

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- p-type substrate of high doping level
- n-type substrate of low doping level
- p-type substrate of moderate doping level
- n-type substrate of high doping level

20. 12. Source and drain in nMOS device are isolated by _____

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- a single diode
- two diodes
- three diodes
- four diodes

21. 13. What is the condition for non saturated region?

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- $V_{ds} = V_{gs} - V_t$
- V_{gs} lesser than V_t
- V_{ds} lesser than $V_{gs} - V_t$
- V_{ds} greater than $V_{gs} - V_t$

22. 14. What is the condition for non conducting mode?

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- V_{ds} lesser than V_{gs}
- V_{gs} lesser than V_{ds}
- $V_{gs} = V_{ds} = 0$
- $V_{gs} = V_{ds} = V_s = 0$

23. 15. MOS transistor structure is _____

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- symmetrical
- non symmetrical
- semi symmetrical
- pseudo symmetrical

24. 16. Which is the commonly used bulk substrate in nMOS fabrication?

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- either bulk silicon or silicon-on-sapphire
- silicon-di-oxide
- aluminium
- copper

25. 17. Contact cuts are made in _____

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- only source
- only drain
- source, drain and gate
- diffusion layer

26. 18. Silicon-di-oxide is a good insulator.

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- True
- False
- Sometimes
- Never

27. 19. In nMOS, _____ is used to suppress unwanted conduction.

Mark only one oval.

- phosphorus
- boron
- silicon
- oxygen

28. 20. The FPGA refers to _____

Mark only one oval.

- First programmable Gate Array
- Field Programmable Gate Array
- First Program Gate Array
- Field Program Gate Array

29. 21. In which design, all circuitry and all interconnections are designed?

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- full custom design
- semi-custom design
- gate array design
- transistor design

30. 22. In which method regularity is used to reduce complexity?

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- random approach
- hierarchical approach
- algorithmic approach
- semi-design approach

31. 23. Which design is faster?

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- full custom design
- semi-custom design
- gate array design
- transistor design

32. 24. Which type of simulation mode is used to check the timing performance of a design?

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- Behavioural
- Switch-level
- Transistor-level
- Gate-level

33. 25. Which type of device FPGA is?

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- SLD
- SRAM
- EPROM
- PLD

34. 26. In FPGA, vertical and horizontal directions are separated by _____

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- A line
- A channel
- A strobe
- A flip-flop

35. 27. The inputs in the PLD is given through _____

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- NAND gates
- OR gates
- NOR gates
- AND gates

36. 28. The n-type semiconductor have _____ as majority carriers.

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- Holes
- Negative ions
- Electrons
- Positive ions

37. 29. The majority carriers of p-type semiconductor are:

Mark only one oval.

- Holes
- Negative ions
- Electrons
- Positive ions

38. 30. The n-MOS transistor is made up of:

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- N-type source, n-type drain and p-type bulk
- N-type source, p-type drain and p-type bulk
- P-type source, n-type drain and n-type bulk
- P- type source, p-type drain and n-type bulk

39. 31. The drain current is varied by:

Mark only one oval.

- Gate to source voltage
- Gate current
- Source Voltage
- None of the mentioned

40. 32. The n-MOSFET is working as accumulation mode when:

Mark only one oval.

- Gate is applied with positive voltage
- Gate is grounded
- Gate is applied with a negative voltage
- Gate is connected to the source

41. 33. Which MOSFET is generally grounded in a circuit?

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- PMOS
- NMOS
- CMOS
- DMOS

42. 34. The current through the n-MOS transistor will flow when:

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- $V_{gs} > V_{tthreshold}$, $V_{ds}=0$
- $V_{gd} < V_{tthreshold}$, $V_{ds}=0$
- $V_{gs} > V_{tthreshold}$, $V_{ds}>0$
- $V_{gd} > V_{tthreshold}$, $V_{ds}<0$

43. 35. The conduction of current I_{DS} depends on: i) Gate to source voltage ii) Drain to source voltage iii) Bulk to source voltage iv) Threshold voltage v) Dimensions of MOSFET

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- Only i
- Only i, ii and iii
- Only v
- All of the mentioned

44. 36. If the n-MOS and p-MOS of the CMOS inverters are interchanged the output is measured at:

Mark only one oval.

- Source of both transistor
- Drains of both transistor
- Drain of n-MOS and source of p-MOS
- Source of n-MOS and drain of p-MOS

45. 37. What will be the effect on output voltage if the positions of n-MOS and p-MOS in CMOS inverter circuit are exchanged?

Mark only one oval.

- Output is same
- Output is reversed
- Output is always high
- Output is always low

46. 38. The CMOS inverter consists of:

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- Enhancement mode n-MOS transistor and depletion mode p-MOS transistor
- Enhancement mode p-MOS transistor and depletion mode n-MOS transistor
- Enhancement mode p-MOS transistor and enhancement mode p-MOS transistor
- Enhancement mode p-MOS transistor and enhancement mode n-MOS transistor

47. 39. When the input of the CMOS inverter is equal to Inverter Threshold Voltage V_{th} , the transistors are operating in:

Mark only one oval.

- N-MOS is cutoff, p-MOS is in Saturation
- P-MOS is cutoff, n-MOS is in Saturation
- Both the transistors are in linear region
- Both the transistors are in saturation region

48. 40. Which of these invertors is more efficient?

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- Depletion mode n-MOS inverter
- pMOS inverter
- CMOS inverter
- Resistive load nMOS inverter

49. 41. The Fermi potential is the function of:

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- Temperature
- Doping concentration
- Difference between Fermi level and intrinsic Fermi level
- All of the mentioned

50. 42. In positive logic convention, the true state is represented as:

Mark only one oval.

- 1
- 0
- 1
- 0

51. 43. In CMOS logic circuit, the switching operation occurs because:

Mark only one oval.

- Both n-MOSFET and p-MOSFET turn OFF simultaneously for input '0' and turn ON simultaneously for input '1'
- Both n-MOSFET and p-MOSFET turn ON simultaneously for input '0' and turn OFF simultaneously for input '1'
- N-MOSFET transistor turns ON, and p-MOSFET transistor turns OFF for input '1' and N-MOS transistor turns OFF, and p-MOS transistor turns ON for input '0'
- None of the mentioned

52. 44. When both nMOS and pMOS transistors of CMOS logic gates are ON, the output is:

Mark only one oval.

- 1 or Vdd or HIGH state
- 0 or ground or LOW state
- Crowbarred or Contention(X)
- None of the mentioned

53. 45. Total number of inputs in a half adder is _____

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- 2
- 3
- 4
- 1

54. 46. If A and B are the inputs of a half adder, the sum is given by _____

Mark only one oval.

- A AND B
- A OR B
- A XOR B
- A EX-NOR B

55. 47. Half-adders have a major limitation in that they cannot _____

Mark only one oval.

- Accept a carry bit from a present stage
- Accept a carry bit from a next stage
- Accept a carry bit from a previous stage
- Accept a carry bit from the following stages

56. 48. If A, B and C are the inputs of a full adder then the sum is given by _____

Mark only one oval.

- A AND B AND C
- A OR B AND C
- A XOR B XOR C
- A OR B OR C

57. 49. How many AND, OR and EXOR gates are required for the configuration of full adder?

Mark only one oval.

- 1, 2, 2
- 2, 1, 2
- 3, 1, 2
- 4, 0, 1

58. 50. Latch is a device with _____

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- One stable state
- Two stable state
- Three stable state
- Infinite stable states

59. 51. Two stable states of latches are _____

Mark only one oval.

- Astable & Monostable
- Low input & high output
- High output & low output
- Low output & high input

60. 52. The full form of SR is _____

Mark only one oval.

- System rated
- Set reset
- Set ready
- Set Rated

61. 53. The outputs of SR latch are _____

Mark only one oval.

x and y

a and b

s and r

q and q'

62. 54. CMOS technology is used in developing which of the following?

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microprocessors

microcontrollers

digital logic circuits

all of the mentioned

63. 55. In CMOS fabrication, nMOS and pMOS are integrated into the same substrate.

Mark only one oval.

true

false

can't be determined

sometimes true sometimes false

64. 56. Oxidation process is carried out using _____

Mark only one oval.

- high purity oxygen
- low purity oxygen
- sulphur
- nitrogen

65. 57. In CMOS fabrication, the photoresist layer is exposed to _____

Mark only one oval.

- visible light
- ultraviolet light
- infrared light
- fluorescent

66. 58. P-well doping concentration and depth will affect the _____

Mark only one oval.

- threshold voltage
- Vss
- Vdd
- Vgs

67. 59. N-well is formed by _____

Mark only one oval.

- decomposition
- diffusion
- dispersion
- filtering

68. 60. Which statement is false concerning Moore's Law?

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- The term was named for Gordon Moore.
- Gordon Moore was one of the founders of IBM.
- In the 1960s the storage density of integrated circuits on a silicon chip doubled about every year.
- Today, when we speak of Moore's Law we refer to the doubling of computer power every 18 months.

69. 61. How many gates per chip are used in first-generation Integrated Circuits?

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- 3-30
- 30-300
- 300-3000
- More than 3000

70. 62. MOS transistors consist of which of the following?

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- semiconductor layer
- metal layer
- layer of silicon-di-oxide
- all of the mentioned

71. 63. The gate region of transistor does not consist of _____

Mark only one oval.

- semiconductor layer
- insulating layer
- metal layer
- ground layer

72. 64. In N channel MOSFET which is the more negative of the elements?

Mark only one oval.

- source
- gate
- drain
- source and drain

73. 65. Enhancement mode device acts as ____ switch, depletion mode acts as ____ switch.

Mark only one oval.

- open, closed
- closed, open
- open, open
- close, close

74. 66. In P channel MOSFET which is the more positive of the elements?

Mark only one oval.

- a. source
- b. gate
- c. drain
- d. source and drain

75. 67. In the inverter circuit, the output is taken from which part of nMOS and pMOS?

Mark only one oval.

- source - source
- drain - drain
- source - drain
- drain - source

76. 68. Which component is added to the p-type material in order to get the impurity concentration in epitaxial films?

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- Bi-borane (B_2H_2)
- Phosphine (PH_3)
- Boron chloride (BCl_3)
- Phosphorous pentoxide (P_2O_5)

77. 69. Which of the following is used to obtain silicon crystal structure while fabricating Integrating Circuits?

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- Oxidation
- Epitaxial growth
- Photolithography
- Glass wafer preparations

78. 70. For oxidation process, silicon wafers are heated to a high temperature and simultaneously they are exposed to a gas containing _____

Mark only one oval.

- H_2O
- Si
- N_2
- H_2

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